

HIGH VOLTAGE FAST SWITCHING NPN POWER TRANSISTOR

APT13003S

General Description

The APT13003S series are high voltage, high speed switching transistors specially designed for off-line switch mode power supplies with low output power.

The APT13003S series are available in TO-92 and TO-126 packages.

Features

- High Switching Speed
- High Collector-Emitter Voltage
- Low Cost
- Bulk and Ammo Packing TO-92 Package and TO-126 Package

Applications

- Battery Chargers for Mobile Phone
- Standby Power Supply

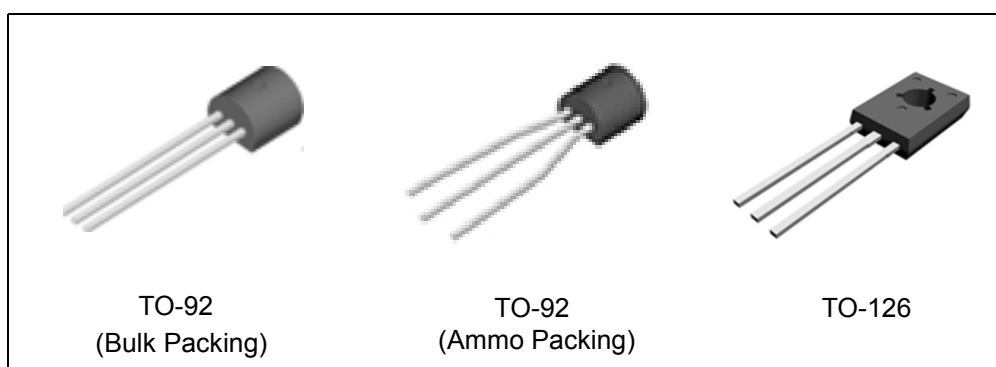
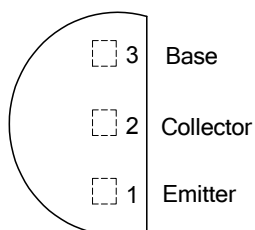


Figure 1. Package Types of APT13003S

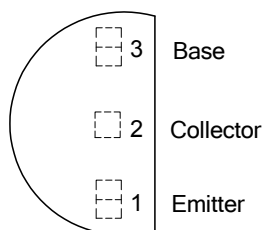
Pin Configuration

Z Package
(TO-92(Bulk Packing))

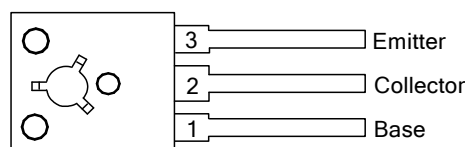


(Top View)

Z Package
(TO-92(Ammo Packing))



U Package
(TO-126)



(Front View)

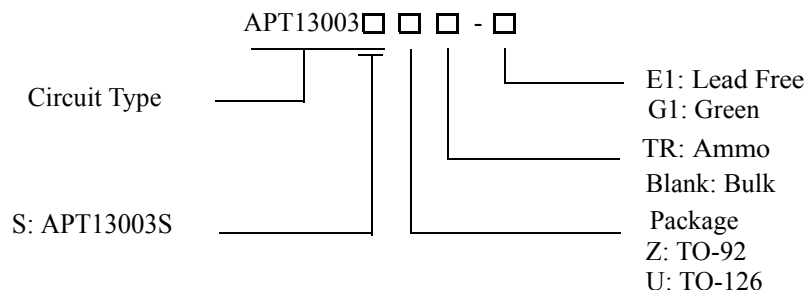
Figure 2. Pin Configurations of APT13003S



HIGH VOLTAGE FAST SWITCHING NPN POWER TRANSISTOR

APT13003S

Ordering Information



Package	Part Number		Marking ID		Packing Type
	Lead Free	Green	Lead Free	Green	
TO-92		APT13003SZ-G1		13003SZ-G1	Bulk
		APT13003SZTR-G1		13003SZ-G1	Ammo
TO-126	APT13003SU-E1	APT13003SU-G1	EU13003S	GU13003S	Bulk

BCD Semiconductor's Pb-free products, as designated with "E1" suffix in the part number, are RoHS compliant. Products with "G1" suffix are available in green packages.

Absolute Maximum Ratings (Note 1)

Parameter	Symbol	Value	Unit	
Collector-Emitter Voltage ($V_{BE}=0$)	V_{CES}	700	V	
Collector-Emitter Voltage ($I_B=0$)	V_{CEO}	450	V	
Emitter-Base Voltage ($I_C=0$)	V_{EBO}	9	V	
Collector Current	I_C	1.3	A	
Collector Peak Current (Pulse) (Note 2)	I_{CM}	2.6	A	
Base Current	I_B	0.65	A	
Base Peak Current (Pulse) (Note 2)	I_{BM}	1.3	A	
Power Dissipation, $T_A=25^\circ\text{C}$	For TO-92	P_{TOT}	1.1	W
Power Dissipation, $T_C=25^\circ\text{C}$	For TO-126	P_{TOT}	20	W
Operating Junction Temperature	T_J	150	$^\circ\text{C}$	
Storage Temperature Range	T_{STG}	-55 to 150	$^\circ\text{C}$	

Note 1: Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "Recommended Operating Conditions" is not implied. Exposure to "Absolute Maximum Ratings" for extended periods may affect device reliability.

Note 2: Pulse test for Pulse Width < 5ms, Duty Cycle ≤ 10%.

**HIGH VOLTAGE FAST SWITCHING NPN POWER TRANSISTOR****APT13003S****Thermal Characteristics**

Parameter		Symbol	Value	Unit
Thermal Resistance (Junction-to-Case)	For TO-92	θ_{JC}	83.3	°C/W
	For TO-126		6.25	
Thermal Resistance (Junction-to-Ambient)	For TO-92	θ_{JA}	113.6	°C/W
	For TO-126		96	

Electrical Characteristics($T_C=25^\circ\text{C}$, unless otherwise specified.)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector Cut-off Current ($V_{BE}=-1.5\text{V}$)	I_{CEV}	$V_{CE}=700\text{V}$			10	μA
Collector-Emitter Sustaining Voltage	$V_{CEO}(\text{sus})$	$I_C=100\mu\text{A}$	450			V
Collector-Emitter Saturation Voltage (Note 3)	$V_{CE}(\text{sat})$	$I_C=0.5\text{A}, I_B=0.1\text{A}$			0.3	V
		$I_C=1.0\text{A}, I_B=0.25\text{A}$			0.6	
Base-Emitter Saturation Voltage (Note 3)	$V_{BE}(\text{sat})$	$I_C=0.5\text{A}, I_B=0.1\text{A}$			1.0	V
		$I_C=1.0\text{A}, I_B=0.25\text{A}$			1.2	
DC Current Gain (Note 3)	h_{FE}	$I_C=0.5\text{A}, V_{CE}=2\text{V}$	13		30	
		$I_C=1.0\text{A}, V_{CE}=2\text{V}$	5		25	
Current Gain Bandwidth Product	f_T	$V_{CE}=10\text{V}, I_C=0.1\text{A}$	4			MHz
Turn-on Time with Resistive Load	t_{on}	$I_C=1\text{A}, V_{CC}=125\text{V}, I_{B1}=0.2\text{A}, I_{B2}=-0.2\text{A}, T_P=25\mu\text{S}$			1.0	μs
Storage Time with Resistive Load	t_s				3.0	
Fall Time with Resistive Load	t_f				0.5	

Note 3: Pulse test for Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$.



Typical Performance Characteristics

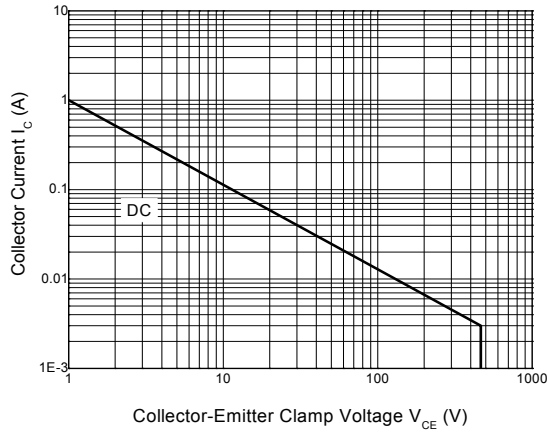


Figure 3. Safe Operating Areas (TO-92 Package)

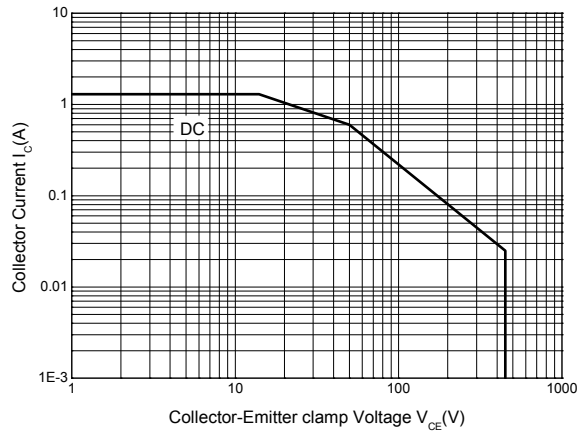


Figure 4. Safe Operating Areas (TO-126 Package)

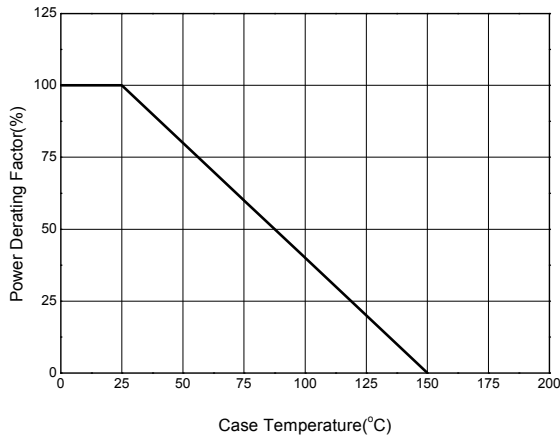


Figure 5. Power Derating Curve

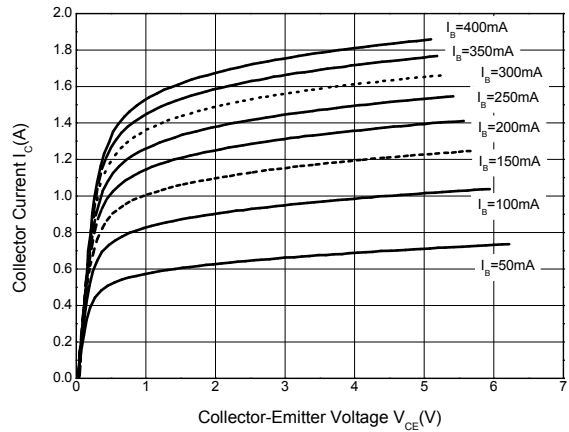


Figure 6. Static Characteristics



Typical Performance Characteristics (Continued)

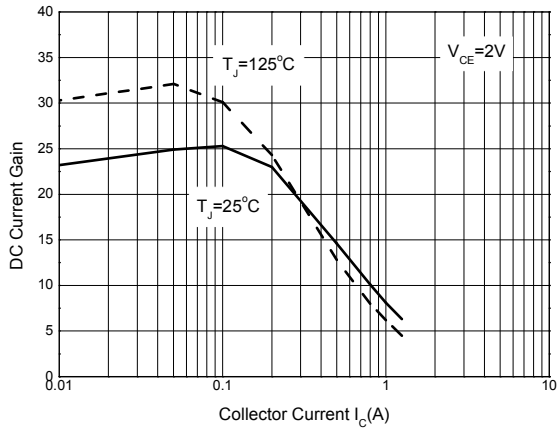


Figure 7. DC Current Gain

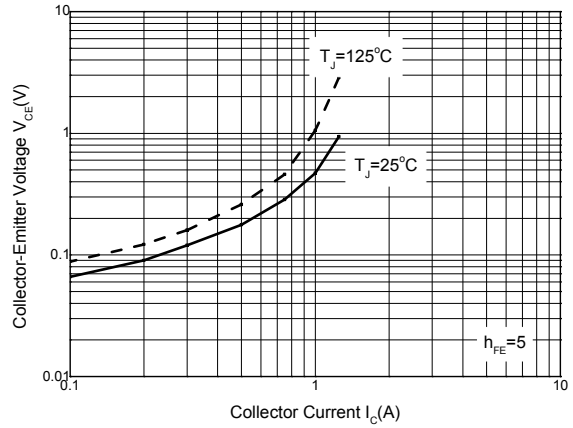


Figure 8. Collector-Emitter Saturation Voltage

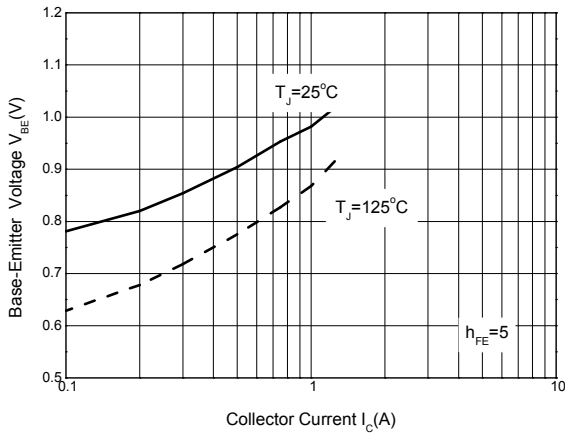


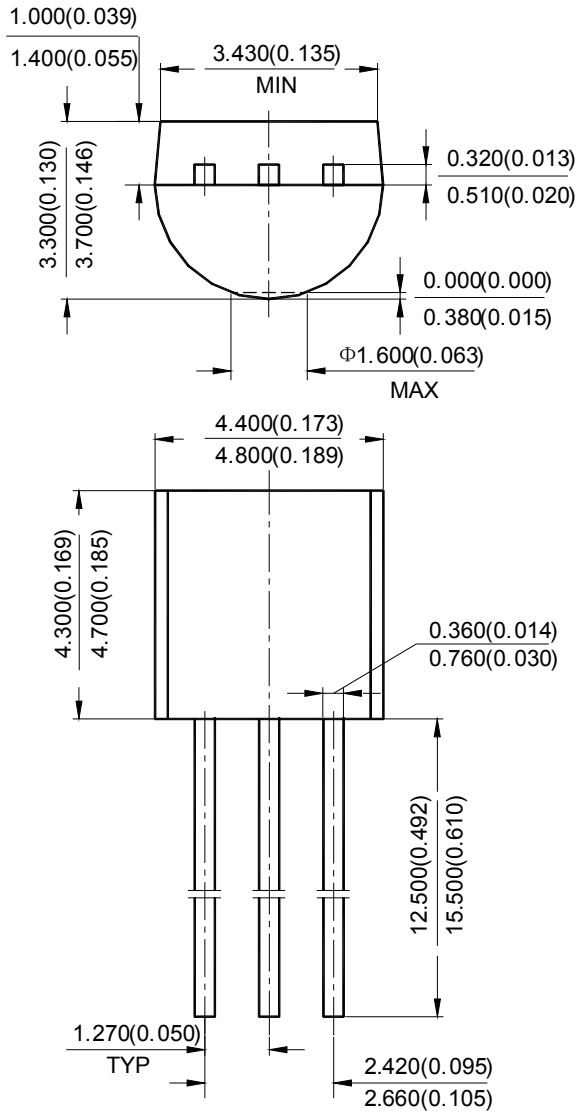
Figure 9. Base-Emitter Saturation Voltage



Mechanical Dimensions

TO-92 (Bulk Packing)

Unit: mm(inch)

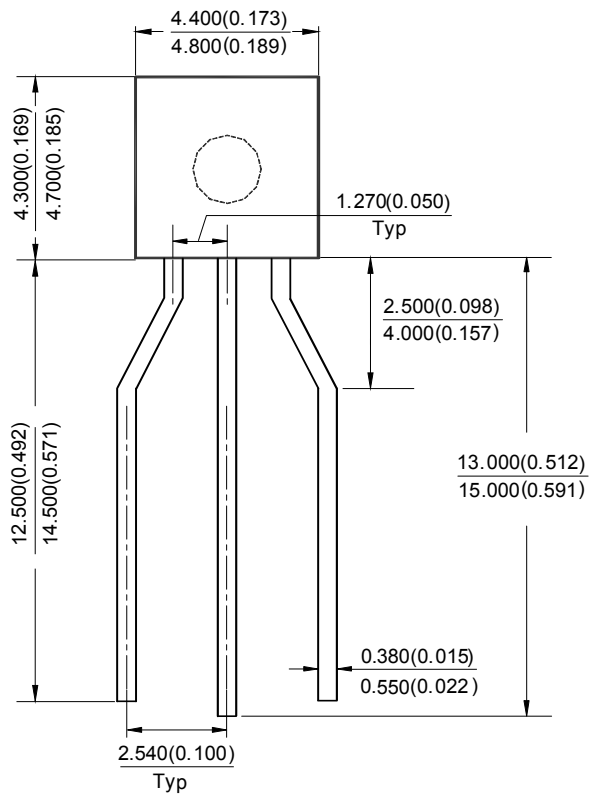
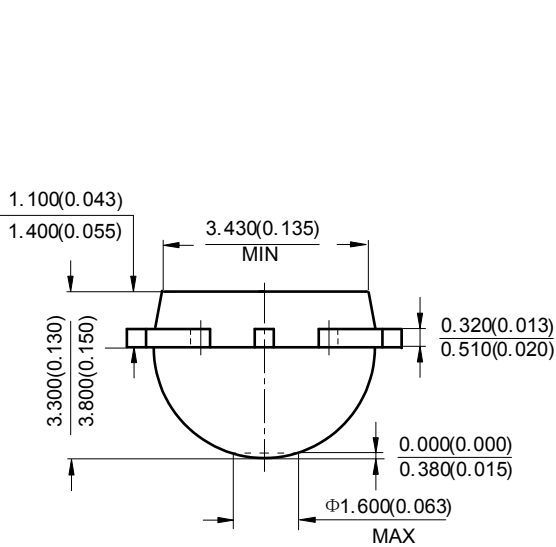




Mechanical Dimensions (Continued)

TO-92 (Ammo Packing)

Unit: mm(inch)

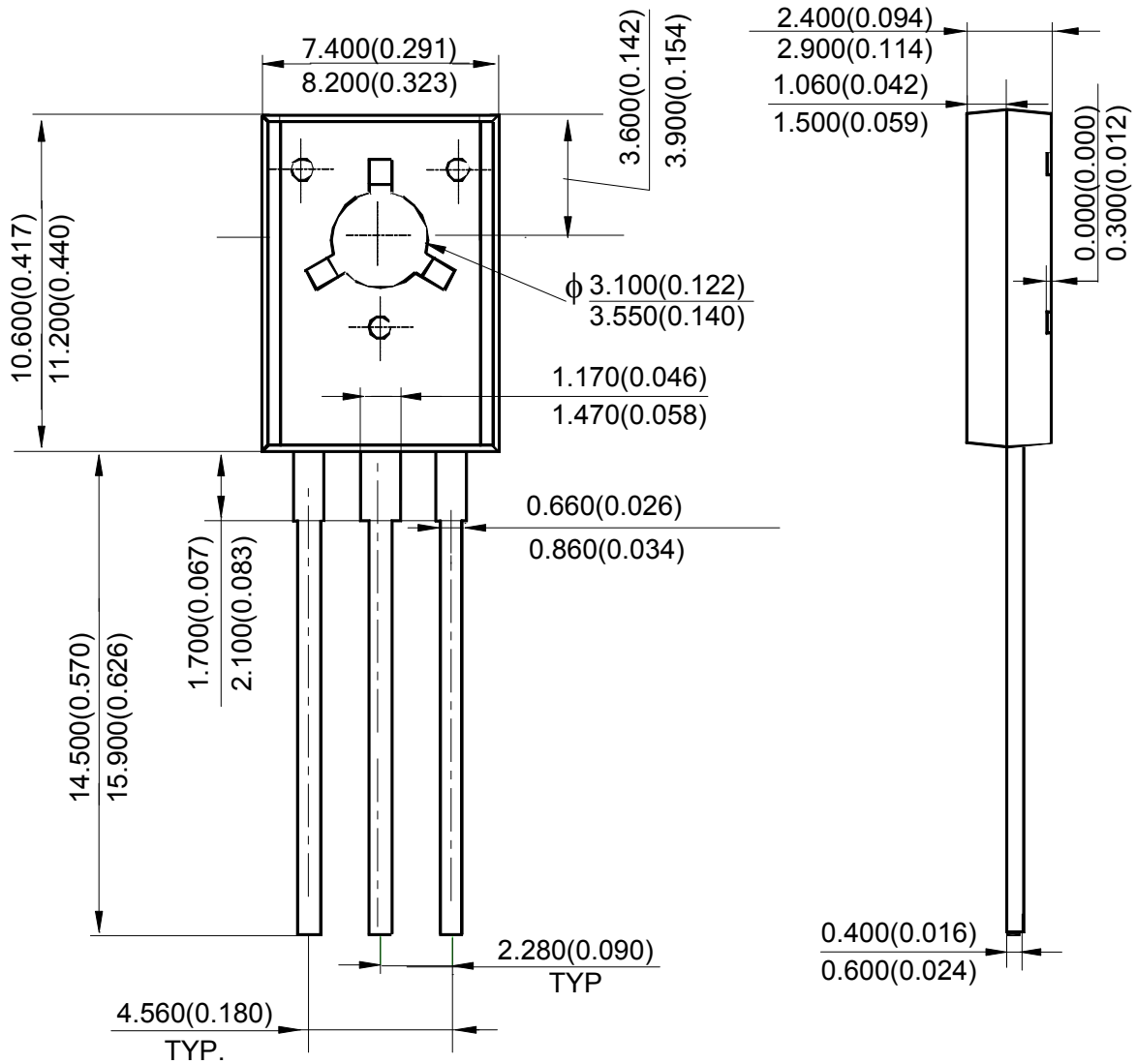




Mechanical Dimensions (Continued)

TO-126

Unit: mm(inch)





BCD Semiconductor Manufacturing Limited

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